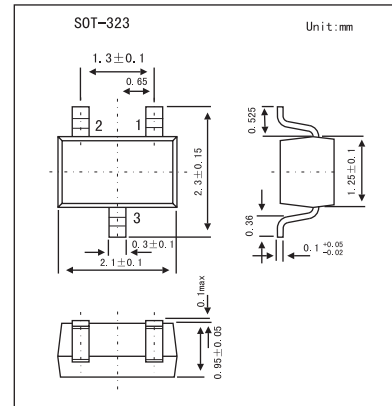


Schottky barrier(double) diodes

BAS70W;BAS70-04W
BAS70-05W;BAS70-06W
■ Features

- Low forward voltage
- High breakdown voltage
- Guard ring protected
- Very small SMD package
- Low capacitance.


■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V _R			70	V
Continuous forward current	I _F			70	mA
Repetitive peak forward current	I _{FRM}	t _p ≤ 1 s; δ ≤ 0.5		70	mA
Non-repetitive peak forward current	I _{FSM}	t _p < 10 ms		100	mA
Storage temperature	T _{stg}		-65	+150	°C
Junction temperature	T _j			150	°C
Operating ambient temperature	T _{amb}		-65	+150	°C
Thermal resistance from junction to ambient	R _{th j-a}	Note 1		625	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Condition	Max	Unit
Forward Voltage	V _F	I _F = 1 mA	410	mV
		I _F = 10 mA	750	mV
		I _F = 15 mA	1	V
Reverse Current	I _R	V _R = 50 V; note 1	100	nA
		V _R = 70 V; note 1	10	μA
Charge carrier life time (Krakauer method)	τ	I _F = 5 mA	100	ps
Diode capacitance	C _d	f = 1 MHz; V _R = 0	2	pF

Note

1. Pulse test: t_p = 300 ms; d = 0.02.

■ Marking

Type	BAS70W	BAS70-04W	BAS70-05W	BAS70-06W
Marking	73*	74*	75*	76*